

FORM PTO 1449 (modified)  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)				ATTY DOCKET NO.  <b>00862.102568.</b>		APPLICATION NO. 10/1510261 U.S. National Stage of PCT/JP2004/018982; filed December 14, 2004	
				APPLICANT  <b>KAZUYA NOTSU, ET AL.</b>			
				FILING DATE  <b>Not Yet Assigned</b>		GROUP 2815 <b>Not Yet Assigned</b>	
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*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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EXAMINER				DATE CONSIDERED 10/10/06			

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

